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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(TYP.)	(mΩ)(TYP.) I _D (A)		
100	2.2 at V _{GS} = 10 V	200	112nC	
	2.6 at V _{GS} = 7.5 V	189	112110	

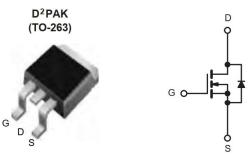
FEATURES

- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- · Motor drive switch
- DC/AC inverter
- Battery management



View	N-Channel MOSFET
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ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage			100	V		
Gate-Source Voltage		V _{GS}	V _{GS} ± 20			
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	1	200	^		
	T _C = 125 °C	⊢ I _D	140			
Pulsed Drain Current (t = 100 μs)		I _{DM}	820	Α		
Avalanche Current	L = 0.1 mH	I _{AS}	110			
Single Avalanche Energy ^a	L = 0.1 IIIn	E _{AS}	625	mJ		
Manianum Daniar Disaination 3	T _C = 25 °C	P _D	395 b	W		
Maximum Power Dissipation ^a	T _C = 125 °C	PD	135 ^b			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.75		

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. 1. 0



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			*	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μА
	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	100	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	=		2	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	200	-		Α
	Б	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	2.2	2.9	mΩ
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 30 \text{ A}$	-	2.6	3.4	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	=	85	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	8440	-	pF
Output Capacitance	C _{oss}		н	1130	-	
Reverse Transfer Capacitance	C _{rss}		-	36	-	
Total Gate Charge ^c	Qg	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 30 A	-	112	-	
Gate-Source Charge ^c	Q _{gs}		-	35.3	-	nC
Gate-Drain Charge ^c	Q _{gd}		-	43.6	-	
Gate Resistance	R_g	f = 1 MHz	-	0.9	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	13	-	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.67 Ω $I_D \cong$ 30 A, V_{GEN} = 10 V, R_g = 1 Ω	-	22	-	
Turn-Off Delay Time ^c	t _{d(off)}		-	27	-	ns
Fall Time ^c	t _f		-	9	-	
Drain-Source Body Diode Ratings ar	d Characteri	stics ^b (T _C = 25 °C)			<u> </u>	
Pulsed Current (t = 100 μs)	I _{SM}		-	8	820	Α
Forward Voltage ^a	V _{SD}	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.86	1.4	V
Reverse Recovery Time	t _{rr}		-	88	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 30 A, di/dt = 100 A/μs	-	5	-	Α
Reverse Recovery Charge	Q _{rr}		_	0.22	_	μC

Notes

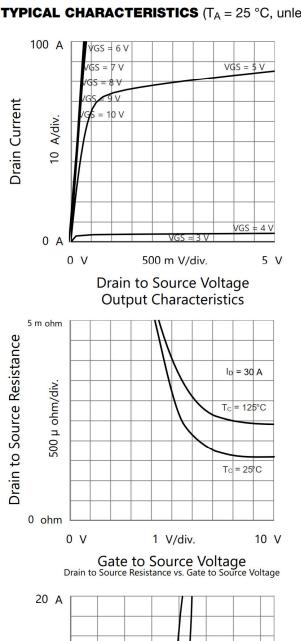
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



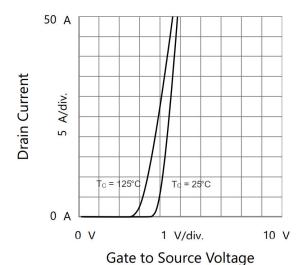
Source Current A/div. Tc = 125°C $T_C = 25^{\circ}C$ 0 A

0 V

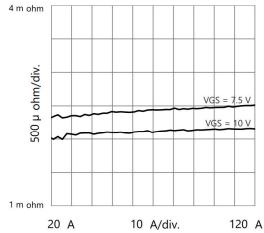
Source to Drain Voltage **Body Diode Forward Characteristics**

200 m V/div.

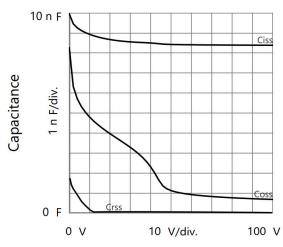
1.5 V



Transfer Characteristics



Drain Current Drain to Source Resistance vs. Drain Current



Drain to Source Voltage Capacitances

10µS

100µS

1mS 100mS

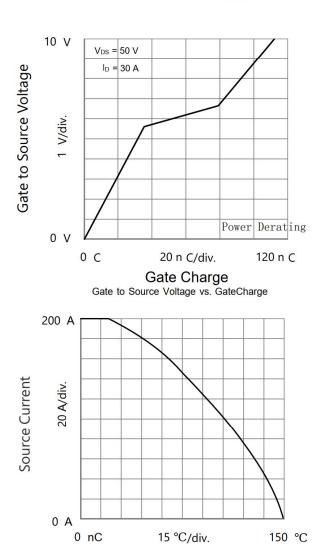
18

DC

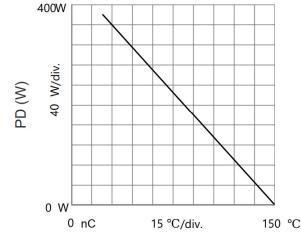
100 V



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



 $T_{C} \textbf{-} \textbf{Case Temperature}_{\text{Current Derating}}$



decade/div.

Source to Drain Voltage

Safe Operating Area, Junction-to-Ambient

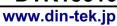
1000 A

decade/div.

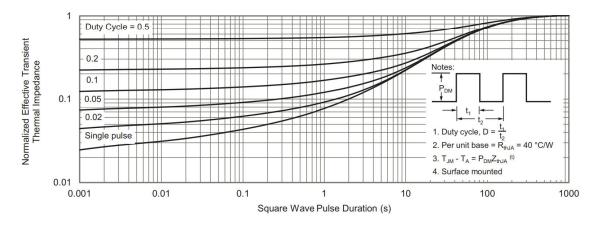
0.1 A

0.01 V

Source Current



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

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- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.





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